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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	5.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104ldafb-30

(2/2)

Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{MAIN} = 20$ MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{MAIN} = 20$ MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels			
	I ² C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		28 sources			29 sources
Event link controller (ELC)		Event input: 19 Event trigger output: 7			Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		• Reset by RESET pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V ($T_A = -40$ to +85°C) 1.51 ±0.06 V ($T_A = -40$ to +105°C) • Power-down-reset: 1.50 ±0.04 V ($T_A = -40$ to +85°C) 1.50 ±0.06 V ($T_A = -40$ to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		$V_{DD} = 1.6$ to 5.5 V ($T_A = -40$ to +85°C) $V_{DD} = 2.4$ to 5.5 V ($T_A = -40$ to +105°C)			
Operating ambient temperature		$T_A = -40$ to +85°C (A: Consumer applications, D: Industrial applications), $T_A = -40$ to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

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Item		80-pin	100-pin
		R5F104Mx (x = F to H, J)	R5F104Px (x = F to H, J)
Code flash memory (KB)		96 to 256	96 to 256
Data flash memory (KB)		8	8
RAM (KB)		12 to 24 Note	12 to 24 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)	
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): $V_{DD} = 1.6$ to 5.5 V	
General-purpose register		8 bits $\times$ 32 registers (8 bits $\times$ 8 registers $\times$ 4 banks)	
Minimum instruction execution time		0.03125 μ s (High-speed on-chip oscillator clock: $f_{IH} = 32$ MHz operation)	
		0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)	
		30.5 μ s (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits $\times$ 8 bits, 16 bits $\times$ 16 bits), Division (16 bits $\div$ 16 bits, 32 bits $\div$ 32 bits) • Multiplication and Accumulation (16 bits $\times$ 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)	

Note In the case of the 24 KB, this is about 23 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

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Item		80-pin	100-pin
		R5F104Mx (x = F to H, J)	R5F104Px (x = F to H, J)
Clock output/buzzer output		2	2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
8/10-bit resolution A/D converter		17 channels	20 channels
D/A converter		2 channels	2 channels
Comparator		2 channels	2 channels
Serial interface		[80-pin, 100-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I²C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I²C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I²C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I²C: 2 channels	
	I ² C bus	2 channels	2 channels
Data transfer controller (DTC)		39 sources	39 sources
Event link controller (ELC)		Event input: 26 Event trigger output: 9	
Vectored interrupt sources	Internal	32	32
	External	13	13
Key interrupt		8	8
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = -40 to +85°C) 1.51 ±0.06 V (T_A = -40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = -40 to +85°C) 1.50 ±0.06 V (T_A = -40 to +105°C)	
Voltage detector		1.63 V to 4.06 V (14 stages)	
On-chip debug function		Provided	
Power supply voltage		V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)	
Operating ambient temperature		T _A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T _A = -40 to +105°C (G: Industrial applications)	

Note The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	0.8 EVDD0		EVDD0	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2	EVDD0	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0	EVDD0	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5	EVDD0	V
	VIH3	P20 to P27, P150 to P156	0.7 VDD		VDD	V
	VIH4	P60 to P63	0.7 EVDD0		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0	0.8	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0	0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0	0.32	V
	VIL3	P20 to P27, P150 to P156	0		0.3 VDD	V
	VIL4	P60 to P63	0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

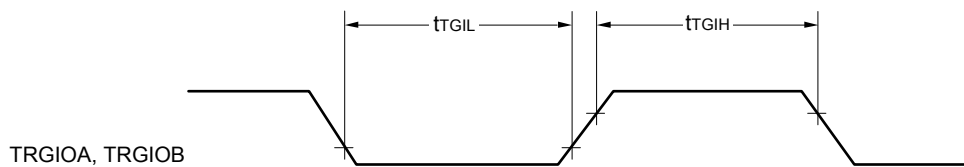
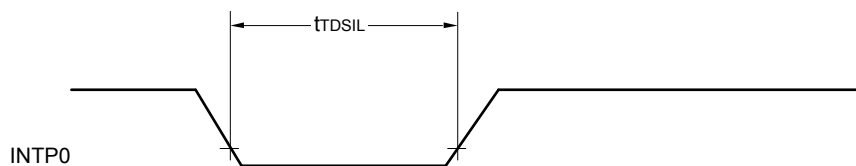
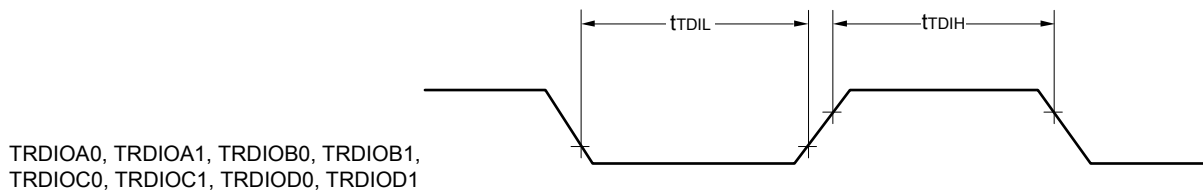
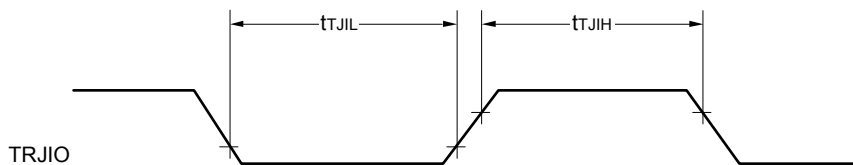
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

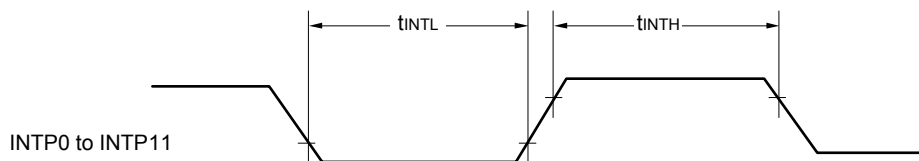
(TA = -40 to +85°C, 1.6 V ≤ EVDD0 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = 0 V)(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit			
Supply current Note 1	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.80	3.09	mA			
					VDD = 3.0 V		0.80	3.09				
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	2.40				
					VDD = 3.0 V		0.49	2.40				
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	2.40				
					VDD = 3.0 V		0.62	2.40				
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	1.83				
					VDD = 3.0 V		0.4	1.83				
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.37	1.38				
					VDD = 3.0 V		0.37	1.38				
			LS (low-speed main) mode Note 7	fHOCO = 8 MHz, fIH = 8 MHz Note 4	VDD = 3.0 V		260	710	μA			
					VDD = 2.0 V		260	710				
			LV (low-voltage main) mode Note 7	fHOCO = 4 MHz, fIH = 4 MHz Note 4	VDD = 3.0 V		420	700	μA			
					VDD = 2.0 V		420	700				
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.28	1.55	mA			
					Resonator connection		0.40	1.74				
					fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.28		1.55		
					Resonator connection		0.40	1.74				
					fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.19		0.86		
					Resonator connection		0.25	0.93				
				fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.19	0.86				
					Resonator connection		0.25	0.93				
				LS (low-speed main) mode Note 7	fMX = 8 MHz Note 3, VDD = 3.0 V	Square wave input		95	550	μA		
						Resonator connection		140	590			
			fMX = 8 MHz Note 3, VDD = 2.0 V		Square wave input		95	550				
					Resonator connection		140	590				
			Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.25	0.57	μA			
					Resonator connection		0.44	0.76				
				fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.30	0.57				
					Resonator connection		0.49	0.76				
				fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.36	1.17				
					Resonator connection		0.59	1.36				
				fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.49	1.97				
					Resonator connection		0.72	2.16				
				fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		0.97	3.37				
					Resonator connection		1.16	3.56				
			IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.18	0.51	μA
					TA = +25°C					0.24	0.51	
					TA = +50°C					0.29	1.10	
					TA = +70°C					0.41	1.90	
					TA = +85°C					0.90	3.30	

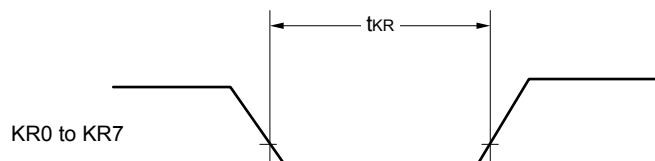
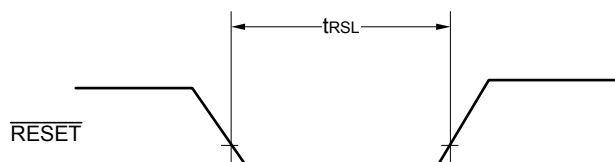
(Notes and Remarks are listed on the next page.)



Interrupt Request Input Timing



Key Interrupt Input Timing

 $\overline{\text{RESET}}$ Input Timing

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	tkCY2	4.0 V ≤ EVDD0 ≤ 5.5 V	20 MHz < fMCK	8/fMCK		—		—		ns
			fMCK ≤ 20 MHz	6/fMCK		6/fMCK		6/fMCK		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	16 MHz < fMCK	8/fMCK		—		—		ns
			fMCK ≤ 16 MHz	6/fMCK		6/fMCK		6/fMCK		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		6/fMCK and 500		6/fMCK and 500		6/fMCK and 500		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		6/fMCK and 750		6/fMCK and 750		6/fMCK and 750		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		6/fMCK and 1500		6/fMCK and 1500		6/fMCK and 1500		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		6/fMCK and 1500		6/fMCK and 1500		ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 7		tkCY2/2 - 7		tkCY2/2 - 7		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 8		tkCY2/2 - 8		tkCY2/2 - 8		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 18		tkCY2/2 - 18		tkCY2/2 - 18		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		tkCY2/2 - 66		tkCY2/2 - 66		tkCY2/2 - 66		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		tkCY2/2 - 66		tkCY2/2 - 66		ns
Slp setup time (to SCKp↑) Note 1	tsIK2	2.7 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 20		1/fMCK + 30		1/fMCK + 30		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 30		1/fMCK + 30		1/fMCK + 30		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 40		1/fMCK + 40		1/fMCK + 40		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		1/fMCK + 40		1/fMCK + 40		ns
Slp hold time (from SCKp↑) Note 2	tkSI2	1.8 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 31		1/fMCK + 31		1/fMCK + 31		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		1/fMCK + 250		1/fMCK + 250		1/fMCK + 250		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		1/fMCK + 250		1/fMCK + 250		ns
Delay time from SCKp↓ to SOp output Note 3	tkSO2	C = 30 pF Note 4	2.7 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 44		2/fMCK + 110		2/fMCK + 110	ns
			2.4 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 75		2/fMCK + 110		2/fMCK + 110	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 100		2/fMCK + 110		2/fMCK + 110	ns
			1.7 V ≤ EVDD0 ≤ 5.5 V		2/fMCK + 220		2/fMCK + 220		2/fMCK + 220	ns
			1.6 V ≤ EVDD0 ≤ 5.5 V		—		2/fMCK + 220		2/fMCK + 220	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EV_{DD0} \geq V_b$.

Note 6. The smaller maximum transfer rate derived by using $f_{mck}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $1.8 \text{ V} \leq EV_{DD0} < 3.3 \text{ V}$ and $1.6 \text{ V} \leq V_b \leq 2.0 \text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(2) I²C fast mode

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fSCL	Fast mode: fCLK ≥ 3.5 MHz	2.7 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	tSU: STA	2.7 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time ^{Note 1}	tHD: STA	2.7 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EVDD0 ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	tHIGH	2.7 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
Data setup time (reception)	tSU: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V		100		100		100		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		100		100		100		ns
Data hold time (transmission) ^{Note 2}	tHD: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tSU: STO	2.7 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		0.6		0.6		0.6		μs
Bus-free time	tBUF	2.7 V ≤ EVDD0 ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V		1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.**Note 2.** The maximum value (MAX.) of tHD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.**Caution** The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.**Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

Operation of products rated “G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$)” at ambient operating temperatures above 85°C differs from that of products rated “A: Consumer applications” and “D: Industrial applications” in the ways listed below.

Parameter	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	$T_A = -40$ to $+85^\circ\text{C}$	$T_A = -40$ to $+105^\circ\text{C}$
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$ LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }8\text{ MHz}$ LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }4\text{ MHz}$	HS (high-speed main) mode only: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
High-speed on-chip oscillator clock accuracy	$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$: $\pm 1.0\%$ @ $T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\%$ @ $T_A = -40$ to -20°C $1.6\text{ V} \leq V_{DD} < 1.8\text{ V}$: $\pm 5.0\%$ @ $T_A = -20$ to $+85^\circ\text{C}$ $\pm 5.5\%$ @ $T_A = -40$ to -20°C	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$: $\pm 2.0\%$ @ $T_A = +85$ to $+105^\circ\text{C}$ $\pm 1.0\%$ @ $T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\%$ @ $T_A = -40$ to -20°C
Serial array unit	UART CSI: $f_{CLK}/2$ (16 Mbps supported), $f_{CLK}/4$ Simplified I ² C communication	UART CSI: $f_{CLK}/4$ Simplified I ² C communication
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage detector	- Rising: 1.67 V to 4.06 V (14 stages) - Falling: 1.63 V to 3.98 V (14 stages)	- Rising: 2.61 V to 4.06 V (8 stages) - Falling: 2.55 V to 3.98 V (8 stages)

Remark The electrical characteristics of products rated “G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$)” at ambient operating temperatures above 85°C differ from those of products rated “A: Consumer applications” and “D: Industrial applications”. For details, refer to 3.1 to 3.10.

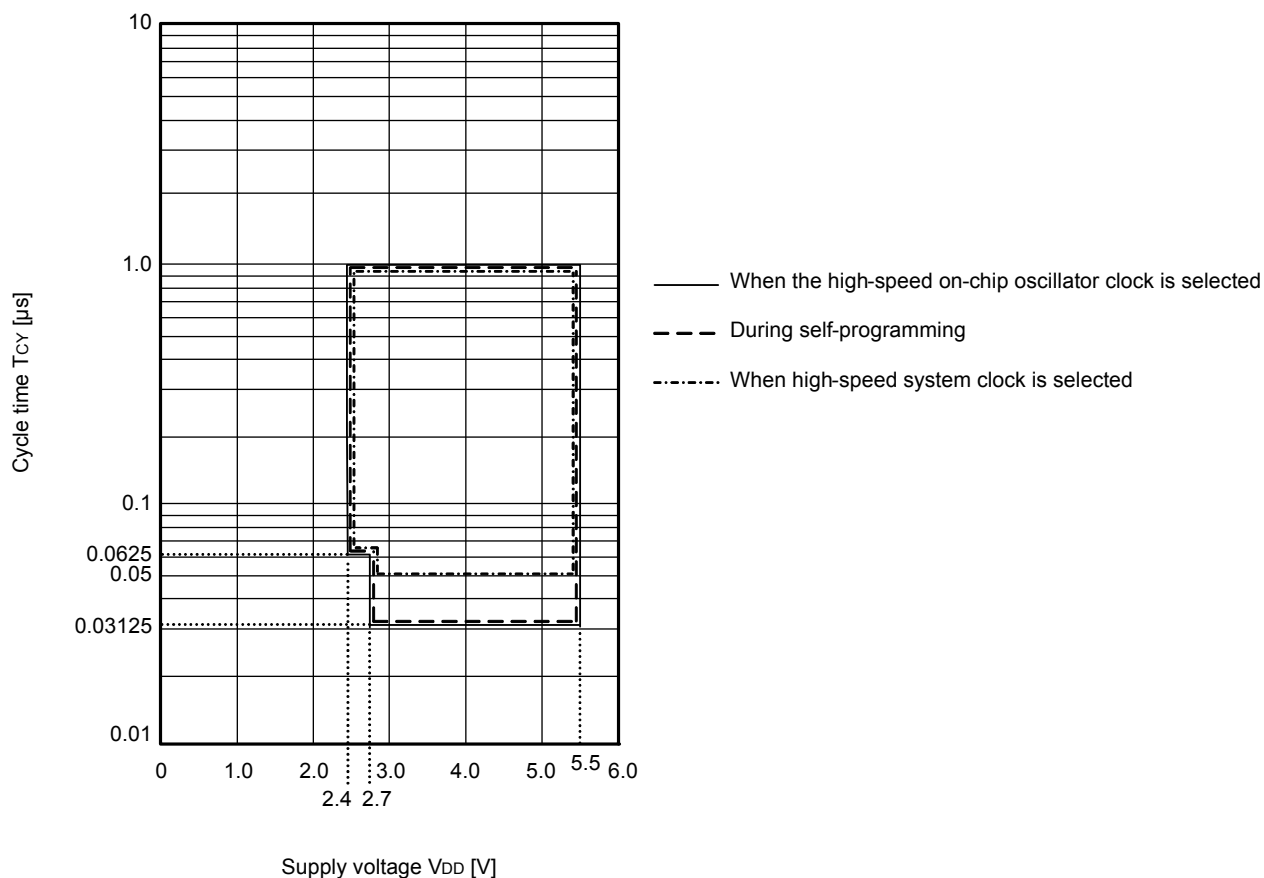
(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = 0\text{ V}$)(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD2 Note 2	HALT mode Note 7	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.80	4.36	mA
					VDD = 3.0 V		0.80	4.36	
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	3.67	
					VDD = 3.0 V		0.49	3.67	
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	3.42	
					VDD = 3.0 V		0.62	3.42	
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	2.85	
					VDD = 3.0 V		0.4	2.85	
			fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.37	2.08		
				VDD = 3.0 V		0.37	2.08		
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.28	2.45	mA
					Resonator connection		0.40	2.57	
				fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.28	2.45	
					Resonator connection		0.40	2.57	
				fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.19	1.28	
					Resonator connection		0.25	1.36	
		fMX = 10 MHz Note 3, VDD = 3.0 V		Square wave input		0.19	1.28		
				Resonator connection		0.25	1.36		
		Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.25	0.57	μA	
				Resonator connection		0.44	0.76		
			fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.30	0.57		
				Resonator connection		0.49	0.76		
			fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.36	1.17		
				Resonator connection		0.59	1.36		
			fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.49	1.97		
				Resonator connection		0.72	2.16		
			fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		0.97	3.37		
				Resonator connection		1.16	3.56		
	fSUB = 32.768 kHz Note 5, TA = +105°C	Square wave input		3.20	17.10				
		Resonator connection		3.40	17.50				
	IDD3 Note 6	STOP mode Note 8	TA = -40°C				0.18	0.51	μA
			TA = +25°C				0.24	0.51	
			TA = +50°C				0.29	1.10	
			TA = +70°C				0.41	1.90	
TA = +85°C				0.90	3.30				
TA = +105°C				3.10	17.00				

(Notes and Remarks are listed on the next page.)

- Note 1.** Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or VSS, EVSS0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

Minimum Instruction Execution Time during Main System Clock Operation

T_{CY} vs V_{DD} (HS (high-speed main) mode)

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	250		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	500		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ EVDD0 ≤ 5.5 V	t _{KCY1} /2 - 24		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	t _{KCY1} /2 - 36		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V	t _{KCY1} /2 - 76		ns
Slp setup time (to SCKp↑) Note 1	t _{SIK1}	4.0 V ≤ EVDD0 ≤ 5.5 V	66		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	66		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V	113		ns
Slp hold time (from SCKp↑) Note 2	t _{SH1}		38		ns
Delay time from SCKp↓ to SOp output Note 3	t _{KS01}	C = 30 pF Note 4		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 Note 1	kHz
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Data setup time (reception)	$t_{\text{SU: DAT}}$	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 220$ Note 2		ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	$1/f_{\text{MCK}} + 580$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD: DAT}}$	$2.7\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.4\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	0	1420	ns

Note 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.**Note 2.** Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	24 MHz < fMCK	28/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	24/fMCK	ns
			8 MHz < fMCK ≤ 20 MHz	20/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	24 MHz < fMCK	40/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	32/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	28/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	24/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	24 MHz < fMCK	96/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	72/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	64/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	52/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	32/fMCK	ns
			fMCK ≤ 4 MHz	20/fMCK	ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	tkCY2/2 - 24		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	tkCY2/2 - 36		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	tkCY2/2 - 100		ns
Slp setup time (to SCKp↑) Note 2	tsIK2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	1/fMCK + 40		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	1/fMCK + 40		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	1/fMCK + 60		ns
Slp hold time (from SCKp↑) Note 3	tsIS2		1/fMCK + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkSO2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		2/fMCK + 240	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		2/fMCK + 428	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rv = 5.5 kΩ		2/fMCK + 1146	ns

(Notes, Caution, and Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)****(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{\text{SU:DAT}}$	$4.0\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$2.7\text{ V} \leq \text{EVDD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$4.0\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.7\text{ V} \leq \text{EVDD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.4\text{ V} \leq \text{EVDD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$1/f_{\text{MCK}} + 570$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$4.0\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.7\text{ V} \leq \text{EVDD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$4.0\text{ V} \leq \text{EVDD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	0	1420	ns
		$2.7\text{ V} \leq \text{EVDD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	1420	ns
		$2.4\text{ V} \leq \text{EVDD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	0	1215	ns

Note 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.**Note 2.** Set the f_{MCK} value to keep the hold time of $\text{SCLr} = \text{"L"}$ and $\text{SCLr} = \text{"H"}$.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/ EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/ EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI16 to ANI20

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$,

$V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.35	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI20		0		AV_{REFP} and EV_{DD0}	V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EV_{DD0} \leq AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Note 4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI20		0		EV_{DD0}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.